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# B.M.S. College of Engineering, Bengaluru-560019

Autonomous Institute Affiliated to VTU

## June 2025 Semester End Main Examinations

**Programme: B.E.**

**Branch: Electrical and Electronics Engineering**

**Course Code: 22EE5PCPE1**

**Course: Power Electronics - I**

**Semester: V**

**Duration: 3 hrs.**

**Max Marks: 100**

**Instructions:** 1. Answer any FIVE full questions, choosing one full question from each unit.  
2. Missing data, if any, may be suitably assumed.

Important Note: Completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages. Revealing of identification, appeal to evaluator will be treated as malpractice.			<b>UNIT - I</b>	<b>CO</b>	<b>PO</b>	<b>Marks</b>
	1	a)	What are the ideal characteristics of switches?	CO3	PO2	06
		b)	Explain the control characteristics of any two power devices.	CO3	PO2	07
		c)	Discuss about peripheral effects of power electronics devices and its remedies.	CO3	PO2	07
			<b>OR</b>			
	2	a)	List explain Ideal and Practical characteristics of power devices	CO1	PO1	10
		b)	With the help of circuit diagram and waveforms explain any two types of power electronic converters	CO3	PO2	10
			<b>UNIT - II</b>			
	3	a)	Explain the reverse recovery characteristics of a diode and derive the expression for reverse recovery current.	CO2	PO3	10
		b)	Evaluate the performance parameters of a single-phase full bridge diode rectifier.	CO2	PO3	10
			<b>OR</b>			
	4	a)	What are the different types of diodes? Explain their constructional features and mention their applications.	CO1	PO1	10
		b)	A single-phase full bridge diode rectifier is connected to a 220V, 50Hz supply. The load resistance is 12.4 Ohms. Calculate i) DC voltage across the load ii) DC load current iii) Ripple factor iv) Power factor v) Peak reverse voltage of each diode	CO2	PO3	10
			<b>UNIT - III</b>			
	5	a)	Explain the structure and working of a BJT	CO1	PO1	08
		b)	Explain the switching characteristics of a BJT.	CO3	PO2	08

	c)	Explain the steady state characteristics of a BJT with relevant graph.	CO1	PO1	04
		<b>OR</b>			
6	a)	Explain the construction and switching characteristics of a MOSFET	CO1	PO1	08
	b)	Compare depletion type and enhancement type MOSFET	CO1	PO1	06
	c)	Describe on SiC MOSFET and comment on its ON-state resistance	CO1	PO1	06
		<b>UNIT - IV</b>			
7	a)	Explain the construction and switching characteristics of an IGBT	CO3	PO2	10
	b)	Explain the steady state characteristics of an IGBT	CO1	PO1	04
	c)	Describe Silicon Carbide IGBT, structure and working.	CO1	PO1	06
		<b>OR</b>			
8	a)	With a neat circuit, explain the turn ON and turn OFF control of a BJT base drive control.	CO4	PO2	07
	b)	Explain the different gate Drive circuits of MOSFET	CO4	PO2	07
	c)	Explain the different gate Drive circuits of IGBT	CO4	PO2	06
		<b>UNIT - V</b>			
9	a)	Explain the V-I characteristics of a thyristor and also define holding current and latching current.	CO1	PO1	08
	b)	Mention different methods of turning ON of a thyristor	CO4	PO2	04
	c)	With the help of a two-transistor model, derive an expression for anode current of a thyristor	CO1	PO1	08
		<b>OR</b>			
10	a)	Describe the structural features of a thyristor? Explain its operation using a suitable model.	CO1	PO1	10
	b)	With the help of circuit diagram and waveforms explain in detail UJT triggering circuit for thyristors.	CO4	PO2	10

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